

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of: Tipton, et al.

Attorney Docket No.:  
NOVLP075/NVLS-000820

Application No.: 10/672,311

Examiner: COLEMAN, WILLIAM D

Filed: September 26, 2003

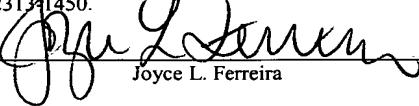
Group: 2823

Title: METHOD OF POROGEN REMOVAL  
FROM POROUS LOW-K FILMS USING  
UV RADIATION

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on April 28, 2005 in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Signed: \_\_\_\_\_

  
Joyce L. Ferreira

**INFORMATION DISCLOSURE STATEMENT  
BEFORE FINAL ACTION OR NOTICE OF ALLOWANCE  
(37 CFR §§ 1.56 AND 1.97(c))**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, a copy of which is attached, may be material to examination of the above-identified patent application. Applicants submit this reference in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make this citation of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that this reference indeed constitutes prior art.

This Information Disclosure Statement is being filed after the mailing date of the first Office Action on the merits, or after three months of the filing date of this application, whichever event occurred last, but it is believed before the mailing date of either: (i) a final action under §1.113 or (ii) a notice of allowance under §1.311, whichever occurs first.

Accompanying this Information Disclosure Statement is

a statement as specified in 37 CFR 1.97(e); or  
 the fee set forth in 37 CFR 1.17(p).

If fees are due, enclosed is our Check No.10573 for \$180.00 in payment of the Information Disclosure Statement Fee. If it is determined that any additional fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP075).

Respectfully submitted,  
BEYER WEAVER & THOMAS, LLP

  
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**Form 1449 (Modified)**
**Information Disclosure  
Statement By Applicant**

(Use Several Sheets if Necessary)

Atty Docket No. NOVLP075/NVLS-000820 Application No.: 10/672,311  
Applicant: Tipton et al.  
Filing Date September 26, 2003 Group 2823

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1A	6,340,628	01/22/02	Van Cleemput, et al.			
	2A	6,383,955	05/07/02	Matsuki, et al.			
	3A	6,596,654	07/22/03	Bayman, et al.			
	4A	4,885,262	12/5/89	Ting et al.			
	5A	5,686,054	11/11/97	Barthel et al.			
	6A	5,851,715	12/22/98	Barthel et al.			
	7A	6,140,252	10/31/00	Cho et al.			
	8A	6,392,017	5/21/02	Chandrashekhar			
	9A	6,386,466	5/14/02	Ozawa et al.			
	10A	4,357,451	11/2/82	McDaniel			
	11A	6,479,374	11/12/02	Ioka et al.			
	12A	6,548,113	4/15/03	Birnbaum et al.			
	13A	6,329,017	12/11/01	Lu et al.			
	14A	2004/0099952	05/27/04	Goodner et al.			
	15A	2004/0102031	05/27/04	Kloster et al.			
	16A	2004/0185679	09/23/04	Ott et al.			

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	17A	Jan, C.H., et al, <i>90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology</i> , 2003 IEEE Interconnect Technology Conference.
	18A	Wu et al., U.S. Application No. 10/789,103 (Atty Docket No.: NOVLP094), entitled: Methods For Producing Low-K Cdo Films With Low Residual Stress
	19A	Wu et al., U.S. Application No. 10/820,525 (Atty Docket No.: NOVLP091), entitled: Methods For Producing Low-K Cdo Films With Low Residual Stress
	20A	Wu et al., U.S. Application No. 10/800,409 (Atty Docket No.: NOVLP098), entitled: Methods For Producing Low-K CDO Films
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)		Atty Docket No. NOVLP075/NVLS-000820	Application No.: 10/672,311
		Applicant: Tipton et al.	
		Filing Date September 26, 2003	Group 2823

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1B	6,848,458	02/01/05	Shrinivasan et al.			02/05/02
	2B	6,805,801	10/19/04	Humayun et al.			03/13/02
	3B	6,391,932	05/21/02	Gore et al.			08/08/00
	4B	5,789,027	08/04/98	Watkins et al.			11/12/96
	5B	5,700,844	12/23/97	Hedrick et al.			04/09/96
	6B	20030157248	08/21/03	Watkins et al.			11/21/02
	7B	20020123240	09/05/02	Gallagher et al.			11/30/01
	8B	20040096672	05/20/04	Lukas et al.			11/14/02

#### Other Documents

	9B	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030)
	10B	U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028)
	11B	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1)
	12B	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064)
	13B	Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Atty Dkt: NOVLP069).

Examiner	Date Considered
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.